

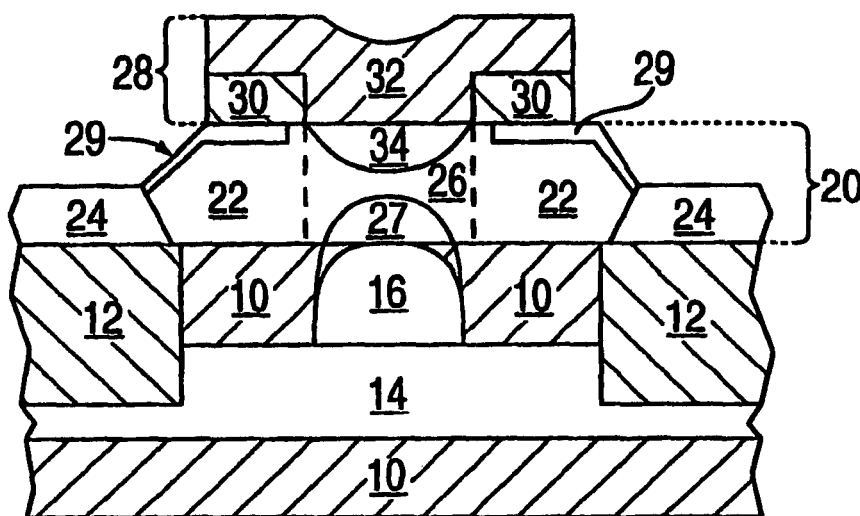


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(54) Title: C IMPLANTS FOR IMPROVED SIGE BIPOLAR TRANSISTORS YIELD



(57) Abstract: A method for improving the SiGe bipolar yield as well as fabricating a SiGe heterojunction bipolar transistor is provided. The inventive method includes ion-implanting carbon C, into at one of the following regions of the device: the collector region (16), the sub-collector region (14), the extrinsic base regions (29), and the collector-base junction region (27). In a preferred embodiment each of the aforesaid regions include C implants.



For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.